PSMN045-100HL

N-channel 100 V, 45 mOhm, logic level MOSFET in LFPAK56D using TrenchMOS technology

26 September 2022 Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology.

2. Features and benefits

- High peak drain current I_{DM}
- Copper clip and flexible Leads
- High operating junction temperature T_j = 175 °C
- Superior reliability
- Low body diode reverse recovery charge Q_r

3. Applications

- Synchronous rectifier
- Forward and flyback converter
- Industrial drive
- Power management system
- Uninterruptible Power Supply (UPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	100	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2		-	-	21	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	53	W
T_j	junction temperature			-55	-	175	°C
Static characteristics FET1 and FET2							
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	38.3	45	mΩ
		V_{GS} = 5 V; I_D = 5 A; T_j = 175 °C; Fig. 12; Fig. 13		-	103	124	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 14; Fig. 15		-	7.3	-	nC
$Q_{G(tot)}$	total gate charge			-	18.5	-	nC
Avalanche ruggedness FET1 and FET2							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 21 A; V_{sup} ≤ 100 V; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; Fig. 4	[1] [2]	-	-	48	mJ

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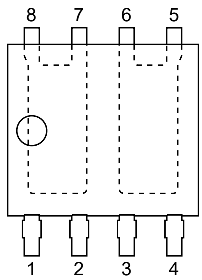
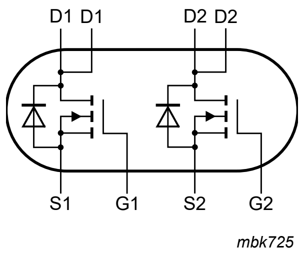
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Source-drain diode FET1 and FET2							
Q_r	recovered charge	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V; T_j = 25 °C		-	42.9	-	nC

[1] Refer to application note AN10273 for further information
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 **LFPAK56D; Dual LFPAK (SOT1205)**	
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN045-100HL	LFPAK56D; Dual LFPAK	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN045-100HL	45RL10H

8. Limiting values

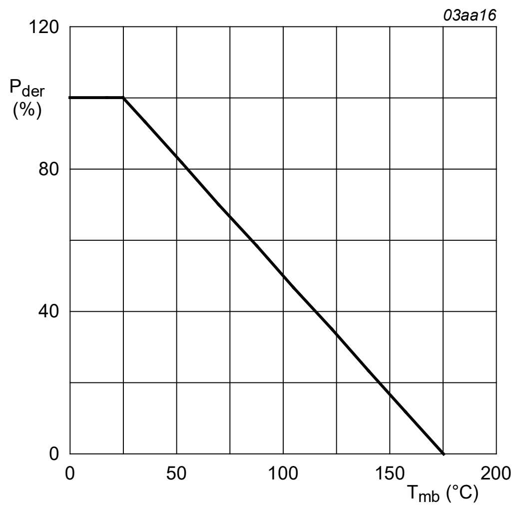
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	100	V
V_{GS}	gate-source voltage	DC; T_j ≤ 175 °C		-10	10	V
		Pulsed; T_j ≤ 175 °C	[1] [2]	-15	15	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	53	W

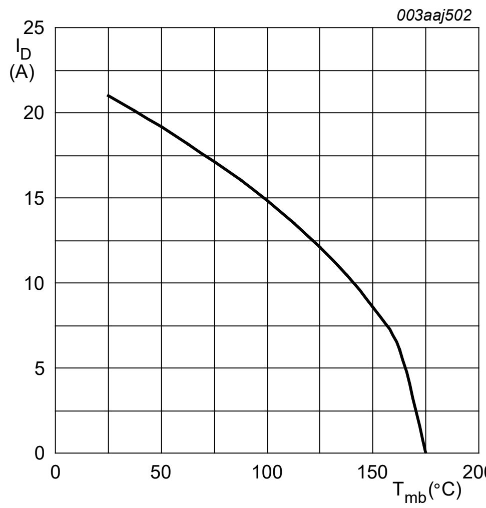
Symbol	Parameter	Conditions		Min	Max	Unit
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2		-	21	A
		V_{GS} = 5 V; T_{mb} = 100 °C; Fig. 2		-	15	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; Fig. 3		-	83	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						
I_S	source current	T_{mb} = 25 °C		-	21	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	83	A
Avalanche ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 21 A; V_{sup} ≤ 100 V; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; Fig. 4	[3] [4]	-	48	mJ

[1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
[2] Significantly longer life times are achieved by lowering T_j and or V_{GS}.
[3] Refer to application note AN10273 for further information
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



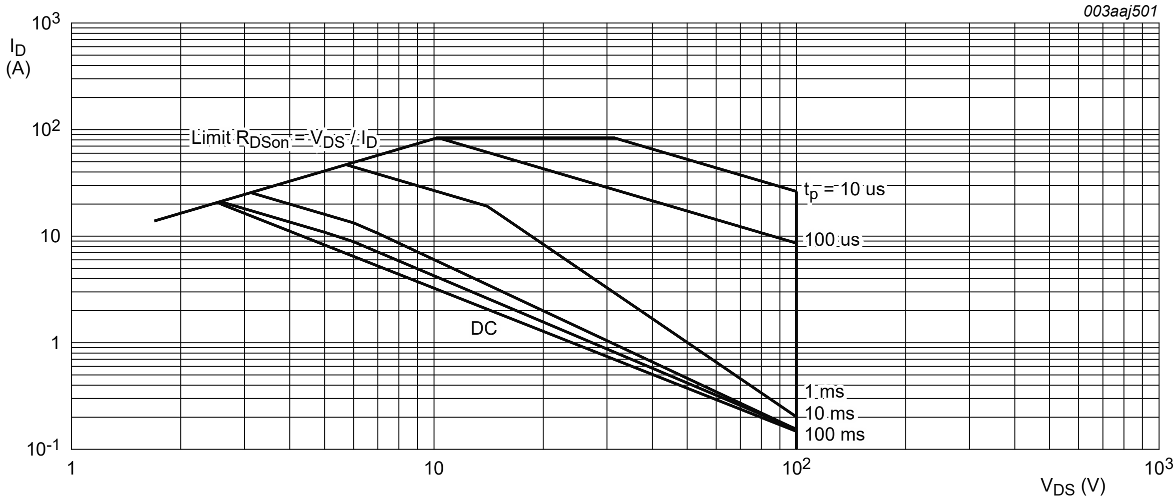
$$P_{der} = \frac{P_{tot}}{P_{tot(25\,°C)}} \times 100\,\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



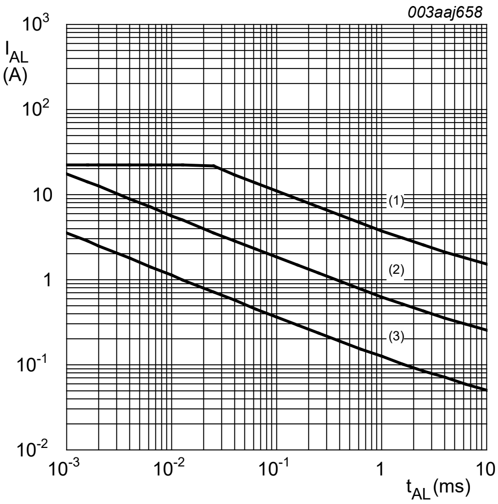
V_{GS} ≥ 5 V

Fig. 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain current as a function of drain-source voltage



(1) $T_{j\,(init)}$ = 25 °C; (2) $T_{j\,(init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	2.84	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	95	-	K/W

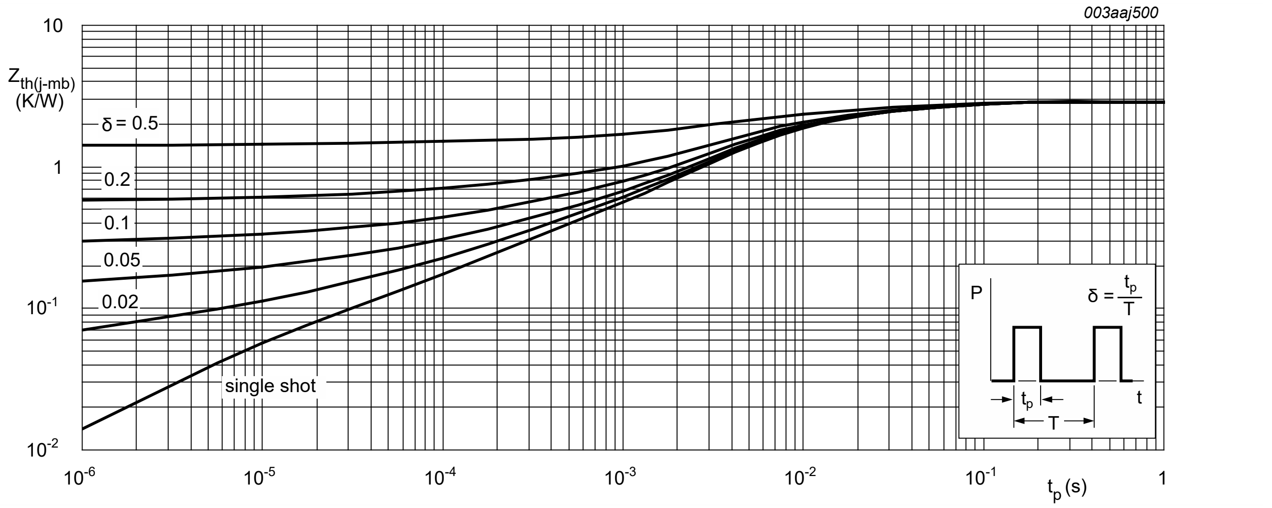


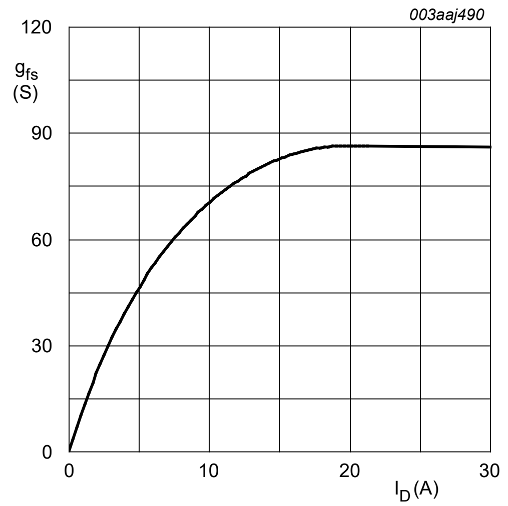
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration

10. Characteristics

Table 7. Characteristics

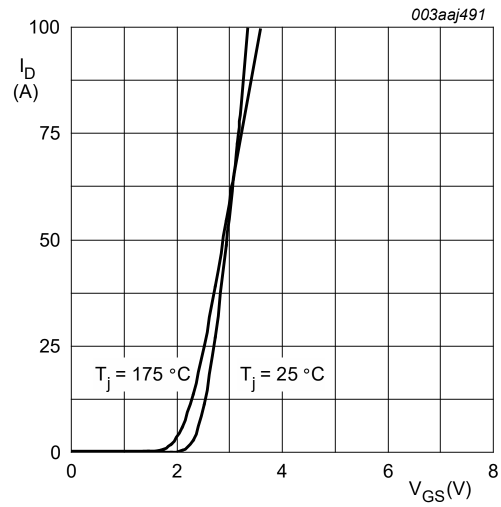
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 °C; Fig. 10; Fig. 11		0.5	-	-	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 °C; Fig. 10; Fig. 11		-	-	2.45	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	1	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	38.3	45	mΩ
		V_{GS} = 5 V; I_D = 5 A; T_j = 175 °C; Fig. 12; Fig. 13		-	103	124	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; Fig. 12		-	35.3	42	mΩ
Dynamic characteristics FET1 and FET2							
$Q_{G(tot)}$	total gate charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 14; Fig. 15		-	18.5	-	nC
Q_{GS}	gate-source charge			-	3.5	-	nC
Q_{GD}	gate-drain charge			-	7.3	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	1614	2152	pF
C_{oss}	output capacitance			-	113	136	pF
C_{rss}	reverse transfer capacitance			-	72	99	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 80 V; R_L = 16 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C		-	10.2	-	ns
t_r	rise time			-	18.1	-	ns

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$t_{d(off)}$	turn-off delay time			-	26.6	-	ns
t_f	fall time			-	17.5	-	ns
Source-drain diode FET1 and FET2							
V_{SD}	source-drain voltage	I_S = 10 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V; T_j = 25 °C		-	29.6	-	ns
Q_r	recovered charge			-	42.9	-	nC



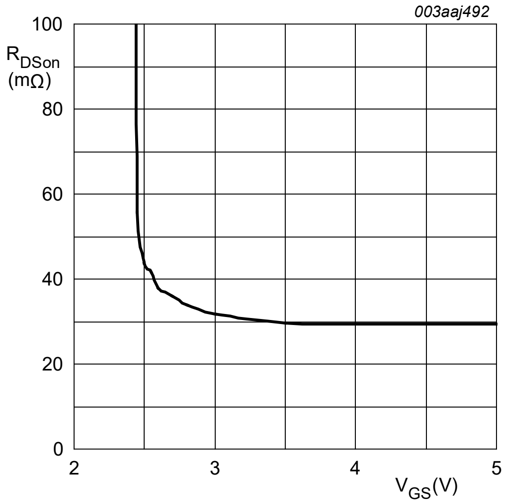
T_j = 25 °C; V_{DS} = 15 V

Fig. 6. Forward transconductance as a function of drain current; typical values



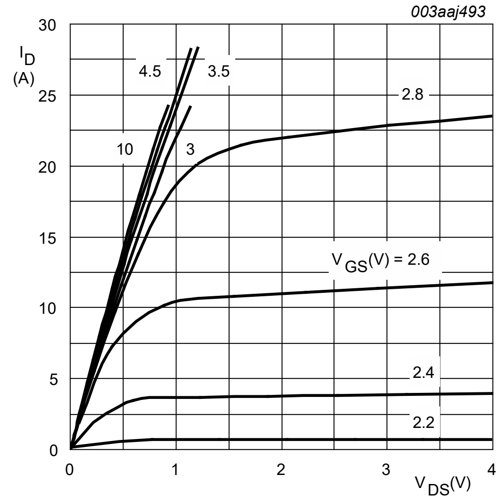
V_{DS} = 10 V

Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



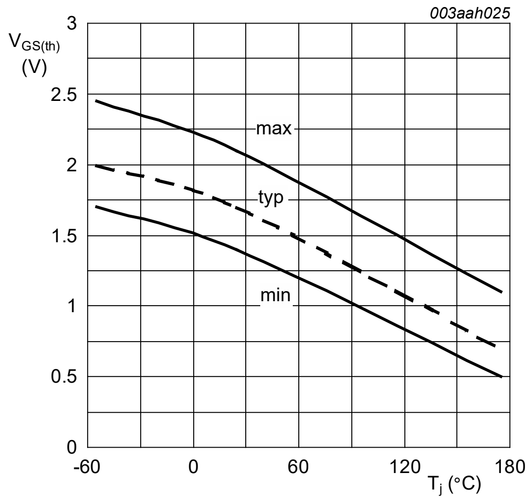
T_j = 25 °C; I_D = 5 A

Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



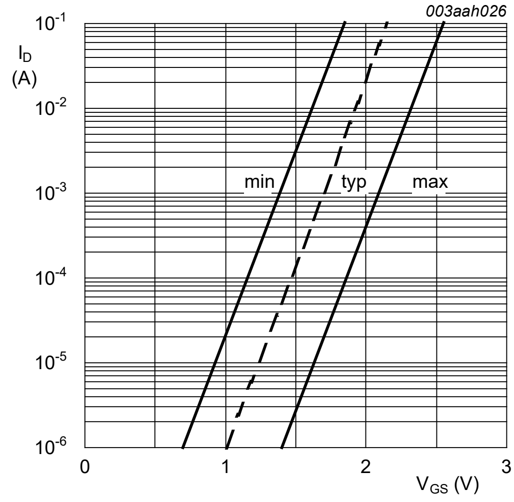
T_j = 25 °C

Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values



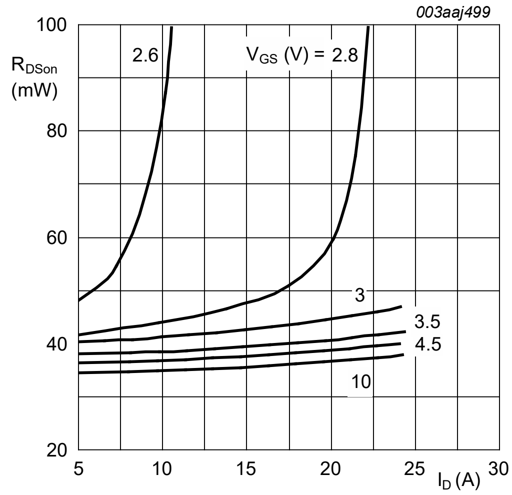
I_D = 1 mA; V_{DS} = V_{GS}

Fig. 10. Gate-source threshold voltage as a function of junction temperature



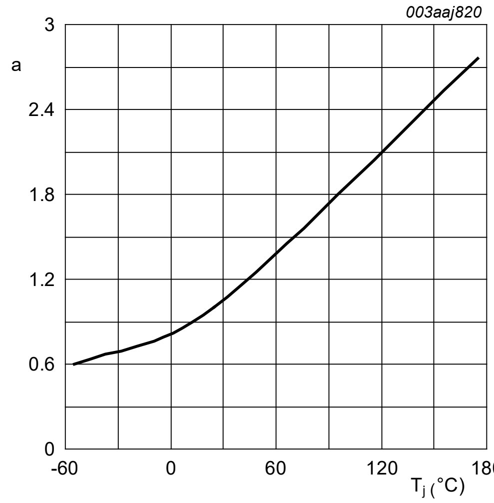
Tj = 25 °C; VDS = 5 V

Fig. 11. Sub-threshold drain current as a function of gate-source voltage



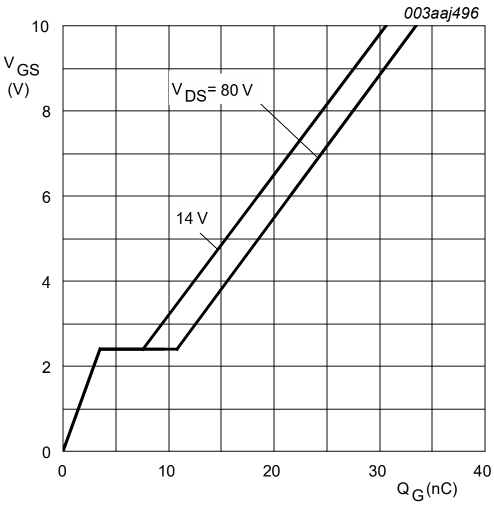
T_j = 25 °C

Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 5 A

Fig. 14. Gate-source voltage as a function of gate charge; typical values

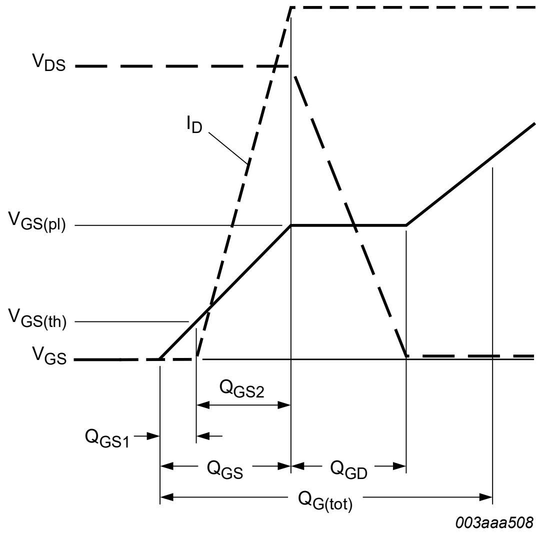
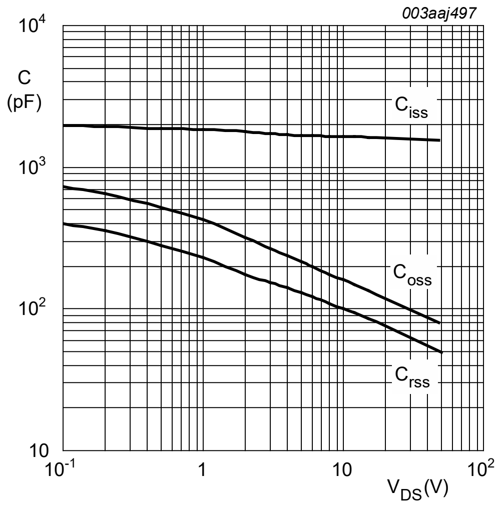
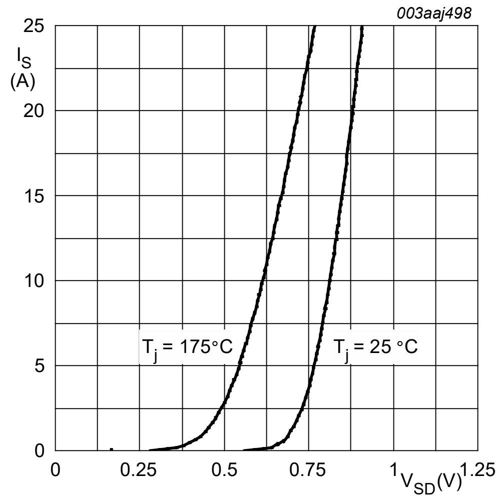


Fig. 15. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

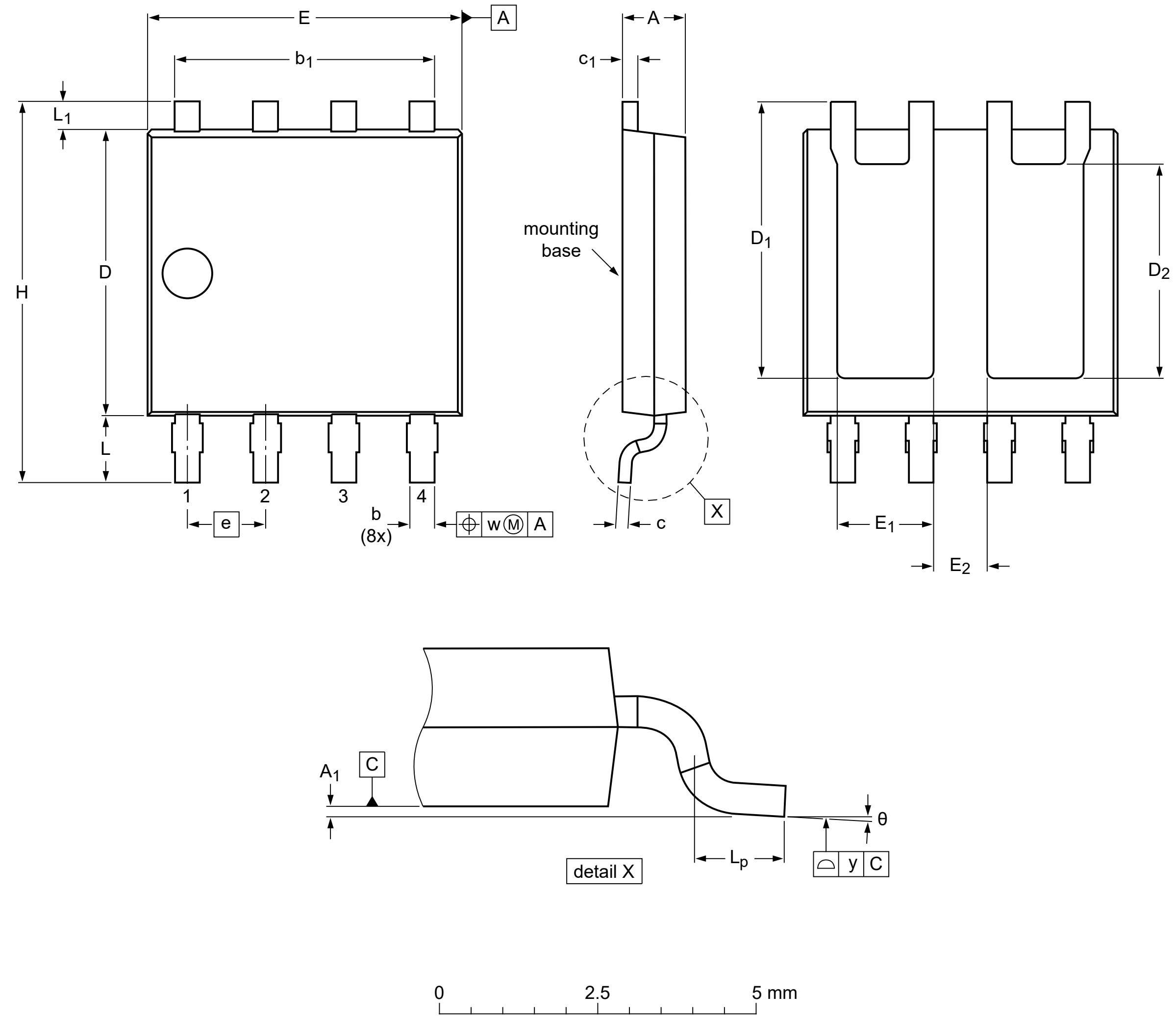


V_{GS} = 0 V

Fig. 17. Source current as a function of source-drain voltage; typical values

11. Package outline

Plastic single ended surface mounted package LFPAK56D; 8 leads **SOT1205**



Dimensions

Unit		A	A_1	b	b_1	c	c_1	$D^{(1)}$	$D_1^{(1)}$	D_2 (ref)	$E^{(1)}$	$E_1^{(1)}$	E_2	e	H	L	L_1	L_p	w	y	θ
mm	max	1.05	0.1	0.50	4.4	0.25	0.30	4.70	4.55	3.5	5.30	1.8	0.85		6.2	1.3	0.55	0.85			8°
	nom													1.27					0.25	0.1	
	min	1.02	0.0	0.35	4.1	0.19	0.24	4.45	4.35	3.4	4.95	1.6	0.60		5.9	0.8	0.30	0.40			0°

Note
1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1205_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1205						~~14-08-21~~ 14-10-28

Fig. 18. Package outline LFPAK56D; Dual LFPAK (SOT1205)

12. Soldering

Footprint information for reflow soldering of LFPAK56D package **SOT1205**

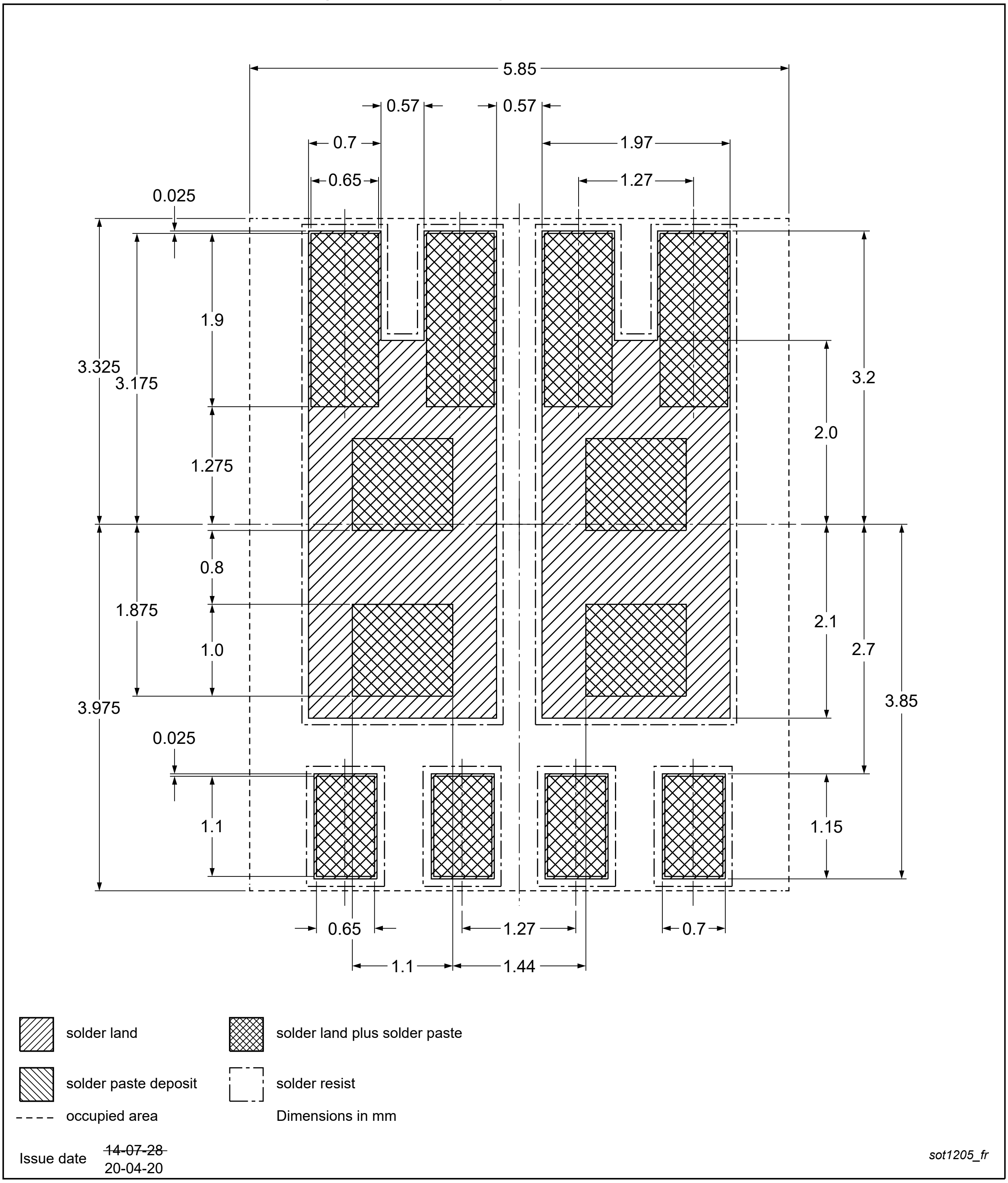


Fig. 19. Reflow soldering footprint for LFPAK56D; Dual LFPAK (SOT1205)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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